

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Title: LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS

Docket No.: 1303.107US1

Filed: June 24, 2003

Examiner: Unknown

Serial No.: 10/602315

Due Date: N/A

Group Art Unit: 2812



Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

X A return postcard.

X An Information Disclosure Statement (2 pgs.), Form 1449 (2 pgs.), and copies of 19 cited documents.

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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
Customer Number 21186

By: David R. Cochran
Atty: David R. Cochran
Reg. No. 46,632

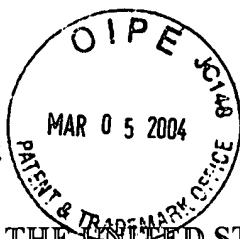
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Judy Mosher
Name

Judy Mosher
Signature

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
(GENERAL)

S/N 10/602315



PATENT

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INFORMATION DISCLOSURE STATEMENT

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Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

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Page 2

Dkt: 1303.107US1

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

KIE Y. AHN ET AL.


By their Representatives,

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By 
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Judy Mosher
Name


Signature

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet 1 of 2

Complete if Known

Application Number	10/602315
Filing Date	June 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2812
Examiner Name	Unknown

Attorney Docket No: 1303.107US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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		LEE, BYOUNG H., et al., "Characteristics of TaN gate MOSFET with ultrathin hafnium oxide (8 A-12 A)", <u>Electron Devices Meeting, 2000. IEDM Technical Digest. International</u> , (2000),39-42	
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EXAMINER

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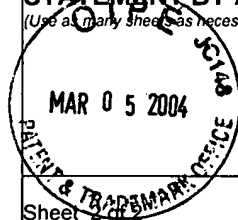
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Sheet 2 of 2

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First Named Inventor Ahn, Kie

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